ZXTP2008Z

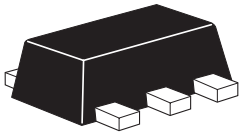
30V PNP LOW SATURATION MEDIUM POWER TRANSISTOR IN SOT89

SUMMARY

BV_{CEO} = -30V : R_{SAT} = 24mΩ; I_C = -5.5A

DESCRIPTION

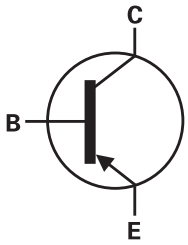
Packaged in the SOT89 outline this new low saturation 30V PNP transistor offers low on state losses making it ideal for use in DC-DC circuits, line switching and various driving and power management functions.



SOT89

FEATURES

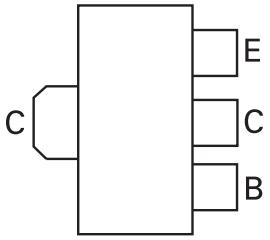
- 5.5 amps continuous current
- Up to 20 amps peak current
- Very low saturation voltages
- Exceptional gain linearity down to 10mA
- Excellent high current gain hold up



APPLICATIONS

- DC - DC converters
- MOSFET gate drivers
- Charging circuits
- Power switches
- Motor control

PINOUT



TOP VIEW

ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXTP2008ZTA	7"	12mm embossed	1000 units

DEVICE MARKING

949

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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Collector-base voltage	BV_{CBO}	-50	V
Collector-emitter voltage	BV_{CEO}	-30	V
Emitter-base voltage	BV_{EBO}	-7	V
Continuous collector current [a]	I_C	-5.5	A
Peak pulse current	I_{CM}	-20	A
Power dissipation at T_A =25°C [a] Linear derating factor	P_D	1.5 12	W mW/°C
Power dissipation at T_A =25°C [b] Linear derating factor	P_D	2.1 16.8	W mW/°C
Operating and storage temperature range	T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE

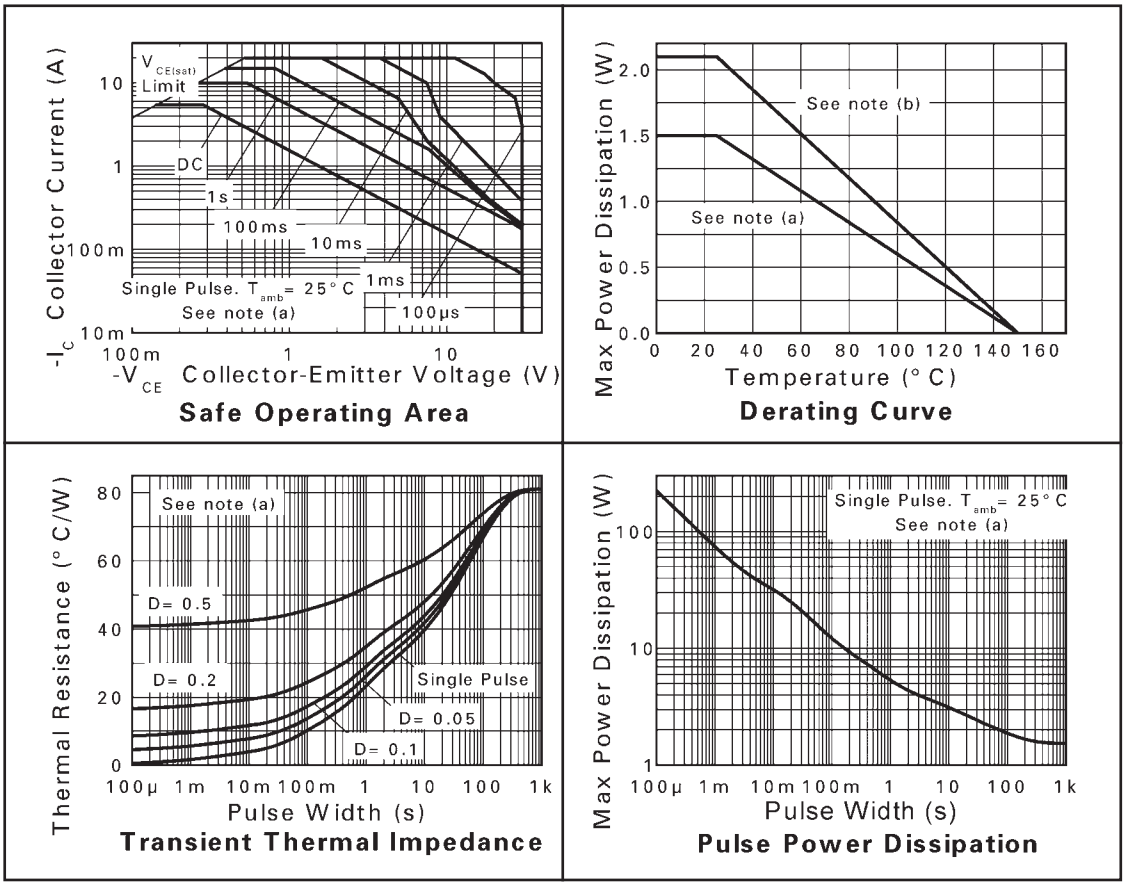
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient [a]	$R_{\Theta JA}$	83	°C/W
Junction to Ambient [b]	$R_{\Theta JA}$	60	°C/W

NOTES

(a) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

CHARACTERISTICS



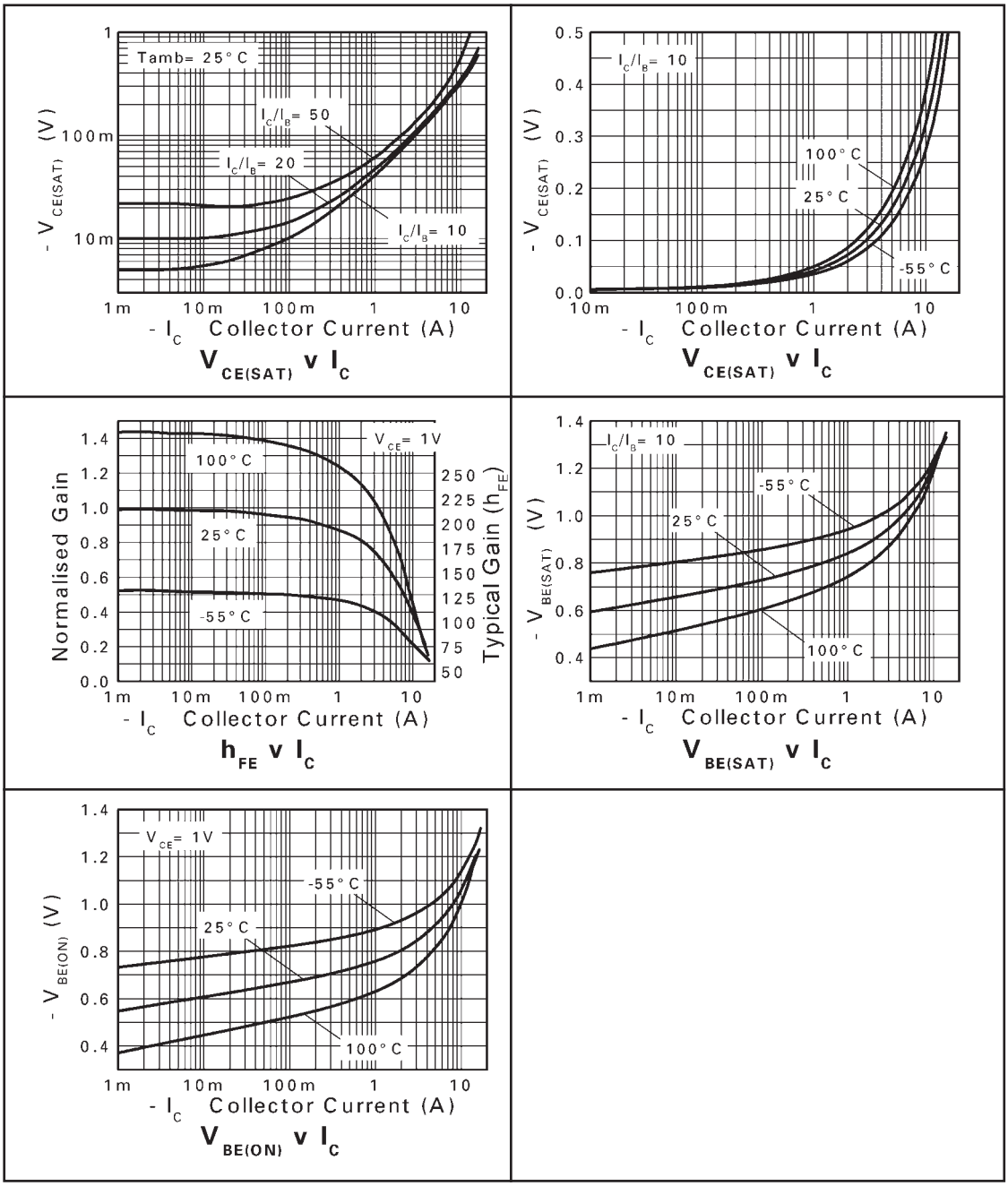
ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Collector-base breakdown voltage	BV_{CBO}	-50	-70		V	I_C = -100μA
Collector-emitter breakdown voltage	BV_{CER}	-50	-70		V	I_C = -1μA, RB <1kΩ
Collector-emitter breakdown voltage	BV_{CEO}	-30	-40		V	I_C = -10mA *
Emitter-base breakdown voltage	BV_{EBO}	-7.0	-8.0		V	I_E = -100μA
Collector cut-off current	I_{CBO}		<-1	-20	nA	V_{CB} = -40V
				-0.5	μA	V_{CB} = -40V,T_{amb} =100°C
Collector cut-off current	I_{CER} R <1kΩ		<-1	-20	nA	V_{CB} = -40V
				-0.5	μA	V_{CB} = -40V,T_{amb} =100°C
Emitter cut-off current	I_{EBO}		<-1	-10	nA	V_{EB} = -6V
Collector-emitter saturation voltage	$V_{CE(SAT)}$		-25	-40	mV	I_C = -0.5A, I_B = -20mA *
			-35	-55	mV	I_C = -1A, I_B = -100mA *
			-55	-80	mV	I_C = -1A, I_B = -20mA *
			-55	-80	mV	I_C = -2A, I_B = -200mA *
			-130	-175	mV	I_C = -5.5A, I_B =-500mA *
Base-emitter saturation voltage	$V_{BE(SAT)}$		-970	-1070	mV	I_C = -5.5A, I_B = -500mA *
Base-emitter turn-on voltage	$V_{BE(ON)}$		-860	-960	mV	I_C = -5.5A, V_{CE} = -1V *
Static forward current transfer ratio	h_{FE}	100	225			I_C = -10mA, V_{CE} = -1V *
		100	200	300		I_C = -1A, V_{CE} = -1V *
		70	145			I_C = -5A, V_{CE} = -1V *
		10	20			I_C = -20A, V_{CE} = -1V *
Transition frequency	f_T		110		MHz	I_C = -100mA, V_{CE} = -10V
						f = 50MHz
Output capacitance	C_{OBO}		83		pF	V_{CB} = -10V, f = 1MHz *
Switching times	t_{ON}		43		ns	I_C = -1A, V_{CC} = -10V,
	t_{OFF}		230			I_{B1} = -I_{B2} = -100mA

NOTES

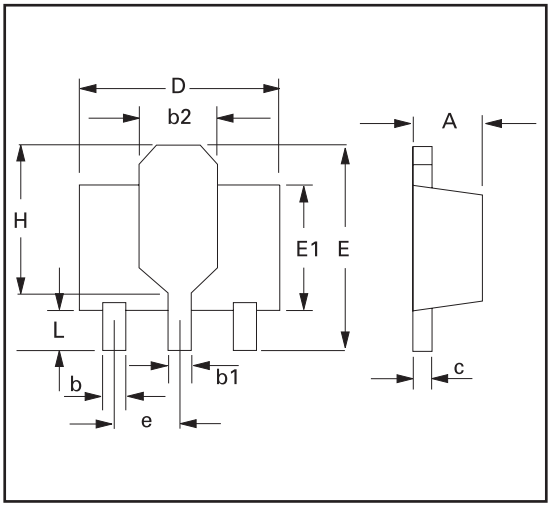
* Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%.

TYPICAL CHARACTERISTICS

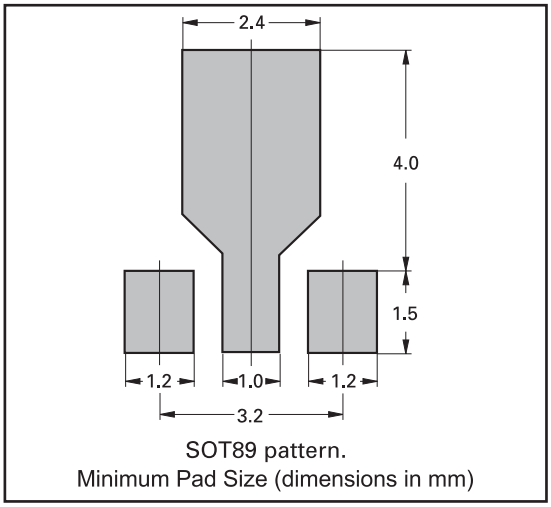


ZXTP2008Z

PACKAGE OUTLINE



PAD LAYOUT DETAILS



SOT89 pattern.
Minimum Pad Size (dimensions in mm)

Controlling dimensions are in millimeters. Approximate conversions are given in inches

PACKAGE DIMENSIONS

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	1.40	1.60	0.550	0.630	e	1.40	1.50	0.055	0.059
b	0.38	0.48	0.015	0.019	E	3.75	4.25	0.150	0.167
b1	-	0.53	-	0.021	E1	-	2.60	-	0.102
b2	1.50	1.80	0.060	0.071	G	2.90	3.00	0.114	0.118
c	0.28	0.44	0.011	0.017	H	2.60	2.85	0.102	0.112
D	4.40	4.60	0.173	0.181	-	-	-	-	-

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Europe

Zetex GmbH
Streitfeldstraße 19
D-81673 München
Germany

Telefon: (49) 89 45 49 49 0
Fax: (49) 89 45 49 49 49
europe.sales@zetex.com

Americas

Zetex Inc
700 Veterans Memorial Hwy
Hauppauge, NY 11788
USA

Telephone: (1) 631 360 2222
Fax: (1) 631 360 8222
usa.sales@zetex.com

Asia Pacific

Zetex (Asia) Ltd
3701-04 Metroplaza Tower 1
Hing Fong Road, Kwai Fong
Hong Kong

Telephone: (852) 26100 611
Fax: (852) 24250 494
asia.sales@zetex.com

Corporate Headquarters

Zetex Semiconductors plc
Zetex Technology Park
Chadderton, Oldham, OL9 9LL
United Kingdom

Telephone (44) 161 622 4444
Fax: (44) 161 622 4446
hq@zetex.com

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